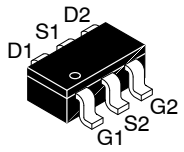
# MOSFET – Specified, Dual P-Channel, POWERTRENCH®

## 2.5 V

# FDC6306P

| $V_{DSS}$ | $R_{DS(ON)}$ MAX | $I_D$ MAX |
|---|---|---|
| −20 V | 0.170 Ω @ −4.5 V | −1.9 A |
| | 0.250 Ω @ −2.5 V | |




**TSOT23 6−Lead**
**SUPERSOT−6**
**CASE 419BL**

### General Description

These P−Channel 2.5 V specified MOSFETs are produced using **onsemi**'s advanced PowerTrench process that has been especially tailored to minimize on−state resistance and yet maintain low gate charge for superior switching performance.

These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO−8 and TSSOP−8 packages are impractical.

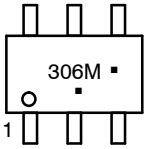
### Features

- −1.9 A, −20 V. $R_{DS(ON)}$ = 0.170 Ω @ $V_{GS}$ = −4.5 V
  $R_{DS(ON)}$ = 0.250 Ω @ $V_{GS}$ = −2.5 V
- Low Gate Charge (3 nC Typical)
- Fast Switching Speed
- High Performance Trench Technology for Extremely Low $R_{DS(ON)}$
- SuperSOT™ −6 Package: Small Footprint (72% Smaller than Standard SO−8); Low Profile (1 mm Thick).
- These Devices are Pb−Free and are RoHS Compliant

### Applications

- Load Switch
- Battery Protection
- Power Management

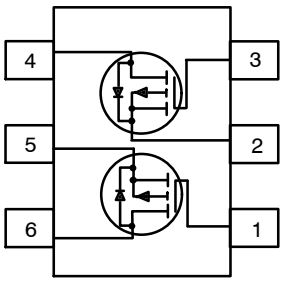
### MARKING DIAGRAM




306 = Specific Device Code
M = Assembly Operation Month
▪ = Pb−Free Package

(Note: Microdot may be in either location)

### PIN CONNECTIONS




### ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C unless otherwise noted)

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $V_{DSS}$ | Drain−Source Voltage | −20 | V |
| $V_{GSS}$ | Gate−Source Voltage | ±8 | V |
| $I_D$ | Drain Current − Continuous (Note 1a)<br>− Pulsed | −1.9<br>−5 | A |
| $P_D$ | Power Dissipation for Single Operation<br>(Note 1a)<br>(Note 1b)<br>(Note 1c) | <br>0.96<br>0.9<br>0.7 | W |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | −55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $R_{\theta JA}$ | Thermal Resistance, Junction−to−Ambient (Note 1a) | 130 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance, Junction−to−Case (Note 1) | 60 | °C/W |

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| FDC6306P | TSOT23 6−Lead (Pb−Free, Halide Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

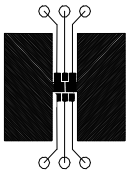
**ELECTRICAL CHARACTERISTICS** ($T_A$ = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain−Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = −250 μA | −20 | – | – | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = −250 μA, Referenced to 25°C | – | −18 | – | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = −16 V, $V_{GS}$ = 0 V | – | – | −1 | μA |
| $I_{GSSF}$ | Gate to Source Leakage Current, Forward | $V_{GS}$ = 8 V, $V_{DS}$ = 0 V | – | – | 100 | nA |
| $I_{GSSR}$ | Gate to Source Leakage Current, Reverse | $V_{GS}$ = −8 V, $V_{DS}$ = 0 V | – | – | −100 | nA |
| **ON CHARACTERISTICS** (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = −250 μA | −0.4 | −0.9 | −1.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D$ = −250 μA, Referenced to 25°C | – | 3 | – | mV/°C |
| $R_{DS(on)}$ | Static Drain−Source On−Resistance | $V_{GS}$ = −4.5 V, $I_D$ = −1.9 A<br>$V_{GS}$ = −4.5 V, $I_D$ = −1.9 A @ $T_J$ = 125°C<br>$V_{GS}$ = −2.5 V, $I_D$ = −1.7 A | –<br>–<br>– | 0.127<br>0.182<br>0.194 | 0.170<br>0.270<br>0.250 | Ω |
| $I_{D(on)}$ | On−State Drain Current | $V_{GS}$ = −4.5 V, $V_{DS}$ = −5 V | −5 | – | – | A |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = −5 V, $I_D$ = −1.9 A | – | 4 | – | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = −10 V, $V_{GS}$ = 0 V, f = 1.0 MHz | – | 441 | – | pF |
| $C_{oss}$ | Output Capacitance | | – | 127 | – | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | – | 67 | – | pF |
| **SWITCHING CHARACTERISTICS** (Note 2) | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = −10V, $I_D$ = −1 A, $V_{GS}$ = −4.5 V, $R_{GEN}$ = 6 Ω | – | 6 | 12 | ns |
| $t_r$ | Turn-On Rise Time | | – | 9 | 18 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | – | 14 | 25 | ns |
| $t_f$ | Turn-Off Fall Time | | – | 3 | 9 | ns |
| $Q_{g(Tot)}$ | Total Gate Charge | $V_{DS}$ = −10 V, $I_D$ = −1.9 A, $V_{GS}$ = −4.5 V | – | 3 | 4.2 | nC |
| $Q_{gs}$ | Gate−Source Charge | | – | 0.7 | – | nC |
| $Q_{gd}$ | Gate−Drain Charge | | – | 0.8 | – | nC |
| **DRAIN−SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS** | | | | | | |
| $I_S$ | Maximum Continuous Drain−Source Diode Forward Current | | – | – | −0.8 | A |
| $V_{SD}$ | Drain−Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = −0.8 A (Note 2) | – | −0.8 | −1.2 | V |

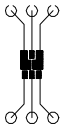
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is the sum of the junction−to−case and case−to−ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.



a. 130°C/W when mounted on a 0.125 $in^2$ pad of 2 oz. copper.



b. 140°C/W when mounted on a 0.005 $in^2$ pad of 2 oz. copper.

c. 180 °C/W when mounted on a 0.0015 in2 pad of 2 oz. copper.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

## TYPICAL CHARACTERISTICS

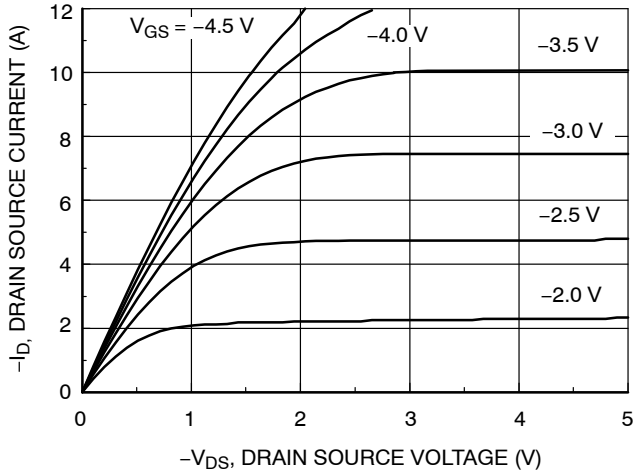



**Figure 1. On−Region Characteristics**

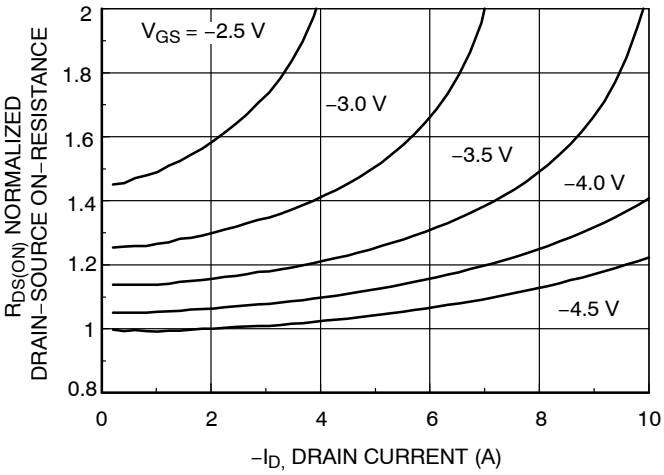



**Figure 2. On−Resistance Variation with Drain Current and Gate Voltage**

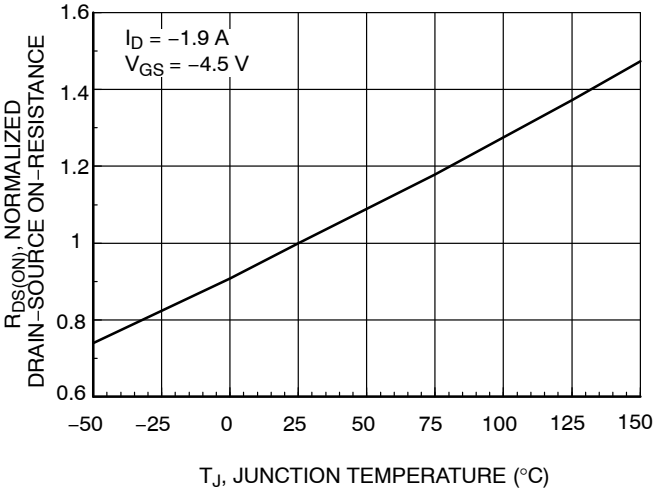



**Figure 3. On−Resistance Variation with Temperature**

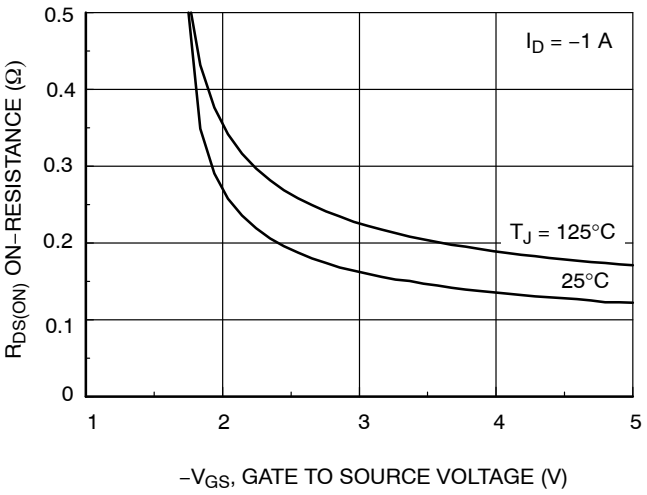



**Figure 4. On−Resistance Variation with Gate−to−Source Voltage**

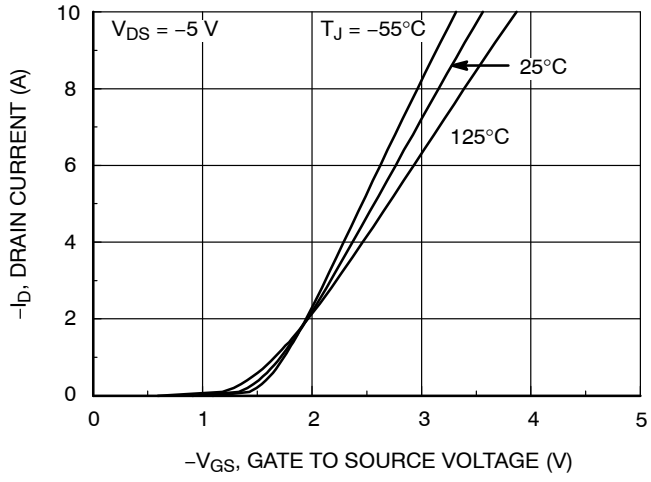



**Figure 5. Transfer Characteristics**

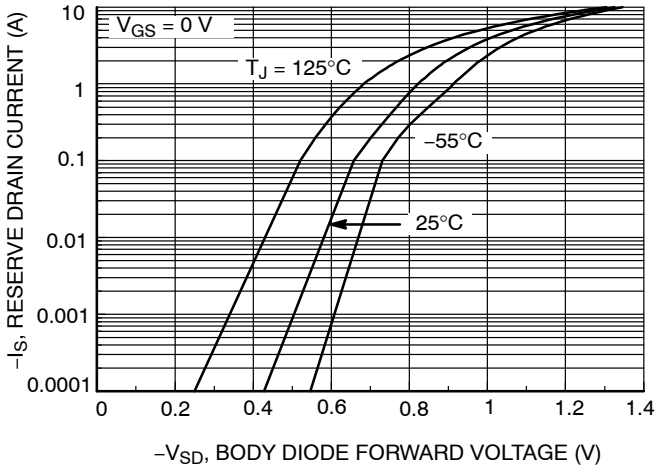



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature**

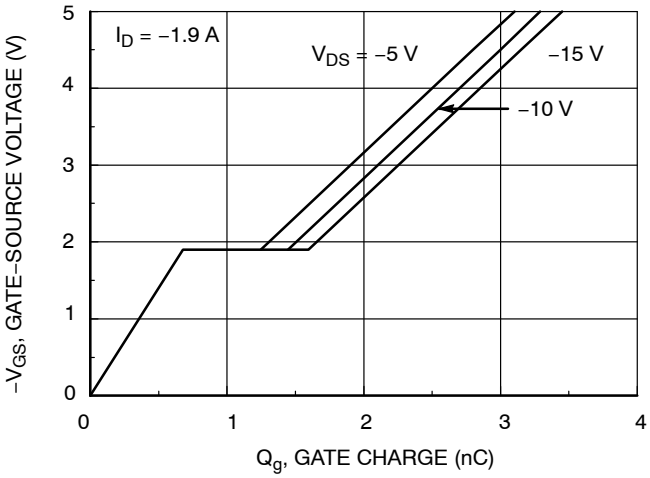



**Figure 7. Gate Charge Characteristics**

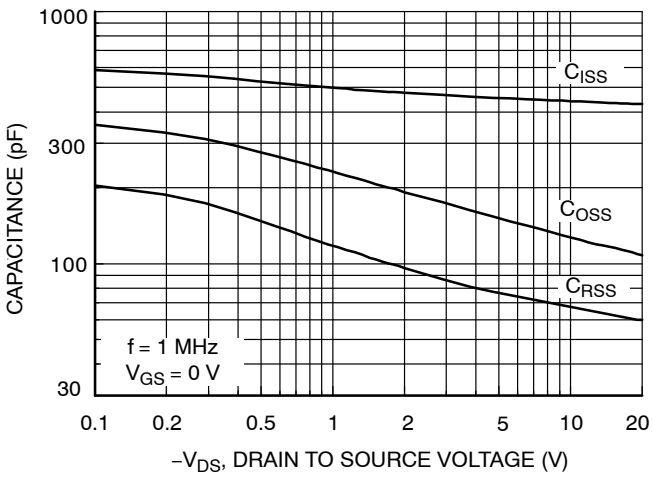



**Figure 8. Capacitance Characteristics**

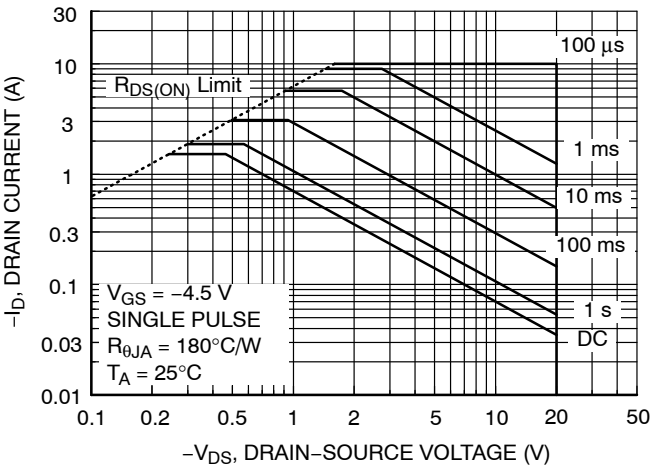



**Figure 9. Maximum Safe Operating Area**

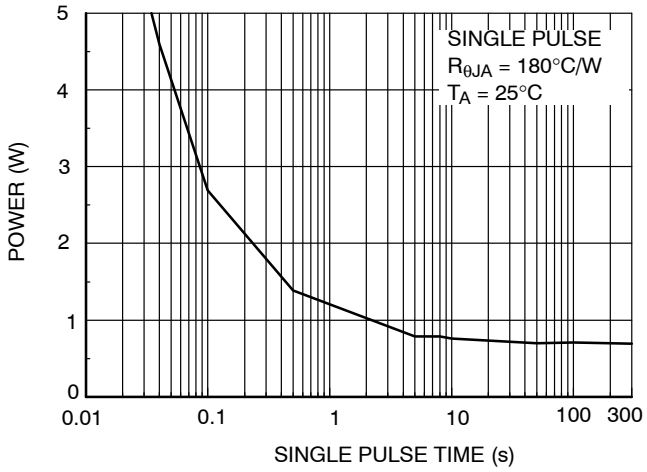



**Figure 10. Single Pulse Maximum Power Dissipation**

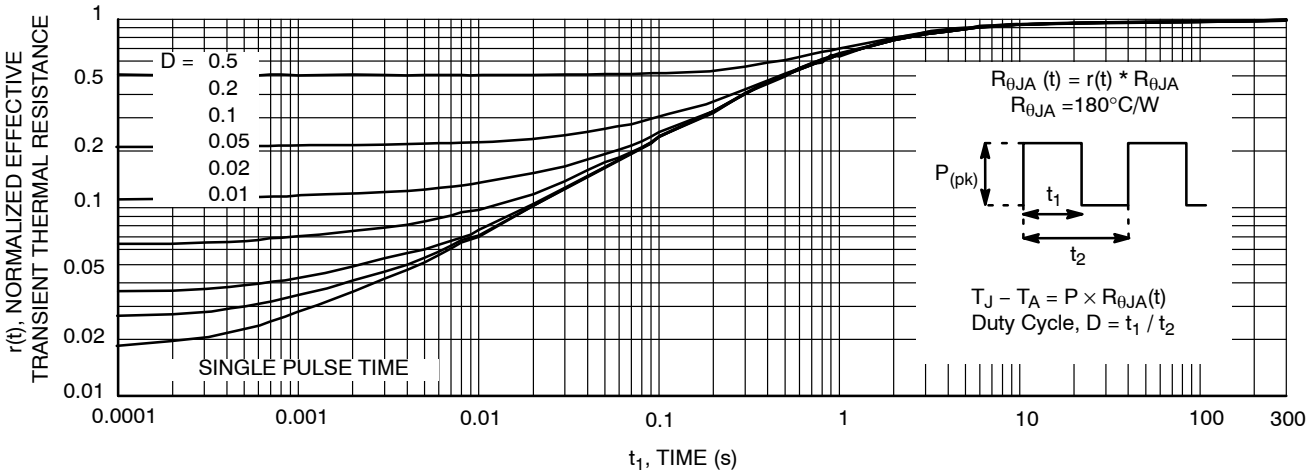



**Figure 11. Transient Thermal Response Curve**

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

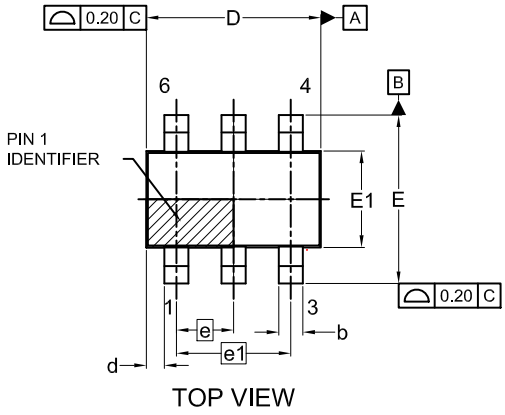
ON Semiconductor®

1

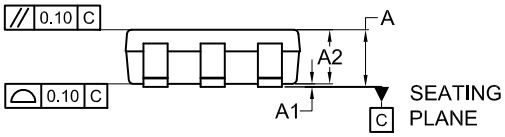
**SCALE 2:1**

**TSOT23 6−Lead**
CASE 419BL
ISSUE A

DATE 31 AUG 2020

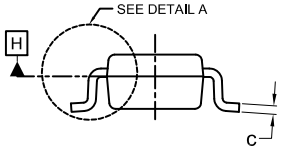



TOP VIEW

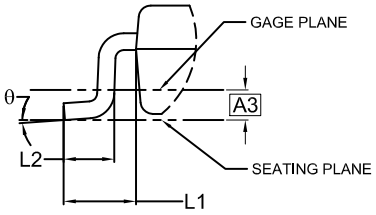



FRONT VIEW

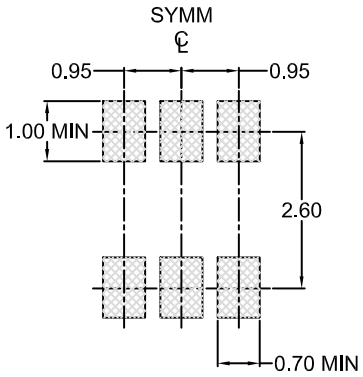
NOTE 4




SIDE VIEW




DETAIL A




LAND PATTERN
RECOMMENDATION

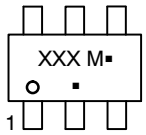
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25MM PER END. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 0.70 | 0.85 | 1.00 |
| A3 | | 0.25 BSC | |
| b | 0.25 | 0.38 | 0.50 |
| c | 0.10 | 0.18 | 0.26 |
| D | 2.80 | 2.95 | 3.10 |
| d | | 0.30 REF | |
| E | 2.50 | 2.75 | 3.00 |
| E1 | 1.30 | 1.50 | 1.70 |
| e | | 0.95 BSC | |
| e1 | | 1.90 BSC | |
| L1 | | 0.60 REF | |
| L2 | 0.20 | 0.40 | 0.60 |
| θ | 0° | --- | 10° |

**GENERIC MARKING DIAGRAM***




XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON83292G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **TSOT23 6−Lead** | **PAGE 1 OF 1** |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales